## **AMENDMENTS TO THE SPECIFICATION:**

Please amend paragraph [0036] as follows:

--As discussed in greater detail herein with respect to Figure 3, an optional step is provided whereby a sacrificial gate oxide layer is first grown prior to depositing the TTO nitride liner 28 50. Alternately, the sacrificial oxide may be grown and removed away after the nitride liner is removed from the channel region just before gate oxidation.--